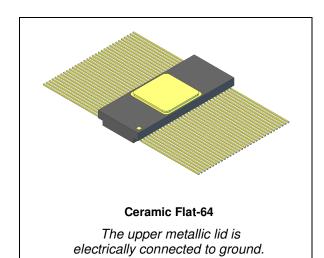




# Rad-hard, dual 4x4 crosspoint switch LVDS

#### Datasheet - production data



### **Features**

- LVDS input/output
- Multiple configuration: Mux, repeater and splitter
- ANSI TIA/EIA-644 compliant
- 400 Mbps LVDS (200 MHz)
- 200 MHz clock channel
- Cold spare on all pins
- · Fail-safe function
- 3.3 V operating power supply
- 4.8 V absolute rating
- Hermetic package
- Power consumption: 220 mW at 3.3 V
   Large input common mode: -4 V to +5 V

- Guaranteed up to 300 krad TID
- SEL immune up to 135 MeV.cm²/mg
- SET/SEU immune up to 22 MeV.cm²/mg

### **Description**

The RHFLVDS2281 is an 8-channel, 4x4 crosspoint switch base, on low voltage differential signaling (LVDS) for low-power and high-speed communications. The two 4x4 multiplexers allow connection from any of the four inputs to any of the four outputs.

Packaged and qualified for use in aerospace environments in a low-power, fast-transmission standard, the RHFLVDS2281 operates at 3.3 V power supply (3.6 V max. operating and 4.8 V AMR) and a common mode of -4 V to +5 V. The LVDS outputs operate over a controlled impedance of 100-ohm transmission media that may be printed circuit board traces, back planes, or cables.

The circuit features an internal fail-safe function to ensure a known state in case of an input short circuit or a floating input.

All pins have cold spare buffers to ensure they are in high impedance when  $\rm V_{CC}$  is tied to GND. The RHFLVDS2281 can operate over a wide temperature range of -55 °C to +125 °C and it is housed in an hermetic Ceramic Flat-64 package.

Table 1. Device summary

Reference	SMD pin	Quality level	Package	Lead finish	Mass	EPPL <sup>(1)</sup>	Temp. range
RHFLVDS2281K1	-	Engineering model	Ceramic Flat-64	Gold	1.94 g	-	-55 °C to
RHFLVDS2281K01V	5962F1423401	QML-V flight				Target	125 0

<sup>1.</sup> EPPL = ESA preferred part list

Contents RHFLVDS2281

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# 1 Functional description

Table 2. Mux truth table

SL1	SL2	SL3	SL4	OUT1	OUT2	OUT3	OUT4	Mode	
0	0	0	0	IN1	IN1	IN3	IN3	Splitter	
0	0	0	1	IN1	IN1	IN3	IN4	Splitter/repeater	
0	0	1	0	IN1	IN1	IN1	IN1	Colittor	
0	0	1	1	IN1	IN1	IN4	IN4	Splitter	
0	1	0	0	IN1	IN2	IN3	IN3	Splitter/repeater	
0	1	0	1	IN1	IN2	IN3	IN4	Repeater	
0	1	1	0	IN1	IN2	IN4	IN3	Repeater/switch	
0	1	1	1	IN1	IN2	IN4	IN4	Splitter/repeater	
1	0	0	0	IN2	IN2	IN2	IN2	Splitter	
1	0	0	1	IN2	IN1	IN3	IN4	Switch/repeater	
1	0	1	0	IN2	IN1	IN4	IN3	Switch	
1	0	1	1	IN3	IN3	IN3	IN3	Colittor	
1	1	0	0	IN2	IN2	IN3	IN3	Splitter	
1	1	0	1	IN2	IN2	IN3	IN4	Splitter/repeater	
1	1	1	0	IN4	IN4	IN4	IN4	Splitter	
1	1	1	1	IN2	IN2	IN4	IN4	Spiillei	

Note: 1 A floating SL pin is equivalent to a low logic level

2 Channels 5, 6, 7, and 8 behave like channels 1, 2, 3 and 4 respectively (see also Figure 2)

Table 3. Enable (EN) truth table

EN	Inputs	Outputs			
LIV	(IN+) - (IN-)	OUT+	OUT-		
L	X	Z	Z		
	Vid ≥ 0.1 V	Н	L		
L or floating	Vid ≤ -0.1 V	L	Н		
H or floating (internal pull-up)	-0.1V < Vid < +0.1 V	Unknown			
	Full fail-safe open/short or terminated	Н	L		

Note: Vid = (VIN+)-(VIN-), L = low level, H = high level, X = don't care, Z = high impedance

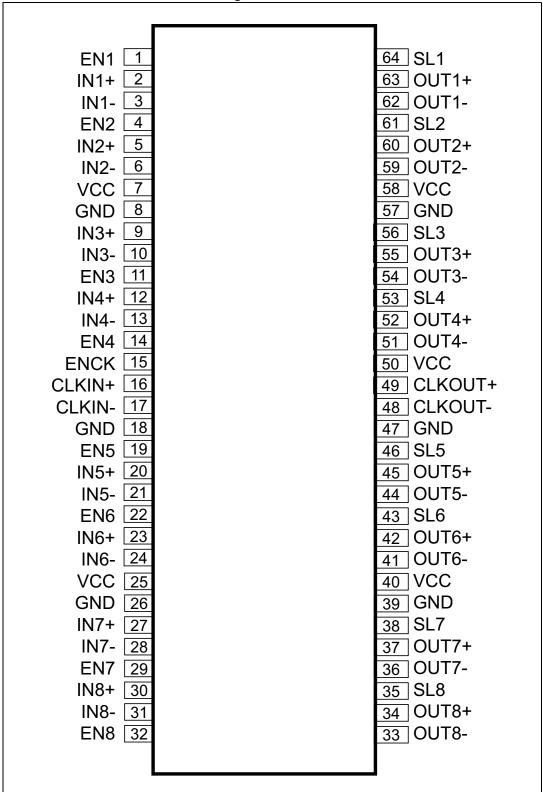


# 2 Internal schematic and pin configuration

EN1 SL1 · OUT1+ IN1+ OUT1-IN1-EN2 SL2 OUT2+ IN2+ OUT2-IN2-MUX 4x4 EN3 SL3 · OUT3+ IN3+ IN3-OUT3-EN4 SL4 OUT4+ IN4+ OUT4-IN4-**ENK** CLKOUT+ CLKIN+ · skew CLKOUT-CLKIN- · match SL5 EN5 IN5+ OUT5+ IN5-OUT5-SL6 EN6 OUT6+ IN6+ IN6-MUX OUT6-4x4 SL7 -EN7 IN7+ OUT7+ OUT7-IN7-SL8 EN8 OUT8+ IN8+ OUT8-IN8-

Figure 1. Internal schematic

Figure 2. Pinout



<sup>1.</sup> Power supplies are not internally separated. All Vcc pins must be connected to the same potential.



# 3 Maximum ratings and operating conditions

Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

Table 4. Absolute maximum ratings

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	Supply voltage <sup>(1)</sup>	4.8		
V <sub>i</sub>	TTL inputs (operating or cold-spare)	-0.3 to +4.8		
V <sub>OUT</sub>	LVDS outputs (operating or coldspare)	-0.3 to +4.8	V	
V <sub>IN</sub>	LVDS inputs (operating or cold-spare)	-5 to +6	-	
V <sub>ID</sub>	Differential amplitude on LVDS input (operating or cold-spare)	1		
T <sub>stg</sub>	Storage temperature range	-65 to +150	°C	
Tj	Maximum junction temperature	+150	O	
R <sub>thjc</sub>	Thermal resistance junction to case <sup>(2)</sup>	20	°C/W	
ESD	HBM: Human body model  - All pins excepted LVDS inputs and outputs  - LVDS inputs and outputs vs. GND	2 8	kV	
	CDM: Charge device model	500	V	

<sup>1.</sup> All voltages, except the differential I/O bus voltage, are with respect to the network ground terminal.

**Table 5. Operating conditions** 

Symbol	Parameter	Min.	Тур.	Max.	Unit		
V <sub>CC</sub>	Supply voltage	3	3.3	3.6	V		
V <sub>CM</sub>	Static common mode	- 4		+ 5	v		
T <sub>A</sub>	Ambient temperature range	-55		+125	°C		

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Short-circuits can cause excessive heating. Destructive dissipation can result from short-circuits on the amplifiers.

### 4 Electrical characteristics

### Total dose (MIL-STD-883 TM 1019)

The products guaranteed in radiation within the RHA QML-V system fully comply with the MIL-STD-883 TM 1019 specification.

The RHFLVDS2281 is RHA QML-V, tested and characterized in full compliance with the MIL-STD-883 specification, between 50 and 300 rad/s only (full CMOS technology).

All parameters provided in *Table 7: Electrical characteristics table* apply to both pre- and post-irradiation, as follows:

- All test are performed in accordance with MIL-PRF-38535 and test method 1019 of MIL-STD-883 for total ionizing dose (TID).
- The initial characterization is performed in qualification only on both biased and unbiased parts.
- Each wafer lot is tested at high dose rate only, in the worst bias case condition, based on the results obtained during the initial qualification.

### **Heavy ions**

The behavior of the product when submitted to heavy ions is not tested in production. Heavy-ion trials are performed on qualification lots only.

Type Characteristics Value Unit TID High-dose rate (50 - 300 rad/sec) 300 krad SEL immunity up to: 135 (with a particle angle of 60°, at 125°C) SEL immunity up to: 67 MeV.cm<sup>2</sup>/mg Heavy ions (with a particle angle of 0 °, at 125 °C) SET/SEU immunity up to: 22 (at 25 °C)

**Table 6. Radiations** 

In *Table 7* below,  $V_{CC}$  = 3 V to 3.6 V, capa-load (CL) = 10 pF, typical values are at  $T_{amb}$  = +25 °C, min. and max values are at  $T_{amb}$  = -55 °C and + 125 °C unless otherwise specified.

Table 7. Electrical characteristics table

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit	
Whole cir	cuit				•		
I <sub>CCL</sub>	Total enabled supply current, drivers and receivers enabled, not switching	$V_{ID}$ = 400 mV and load = 100 $\Omega$ on all channels		67	80	A	
I <sub>CCZ</sub>	Total disabled supply current, loaded or not loaded, drivers and receivers disabled	V <sub>ID</sub> = 400 mV EN and ENCK = GND			20 mA		
Digital in	puts EN, ENCK, and SL		•				
V <sub>IH</sub>	Input voltage high		2		$V_{CC}$	V	
V <sub>IL</sub>	Input voltage low		GND		0.8	V	
I <sub>IH</sub>	High level input current	$V_{CC} = 3.6 \text{ V}, V_{IN} = V_{CC}$	-10		10		
I <sub>IL</sub>	Low level input current	$V_{CC} = 3.6 \text{ V}, V_{IN} = 0$	-10		10	μΑ	
l <sub>OFF</sub>	TTL inputs power off leakage current	V <sub>CC</sub> = 0 V, EN and SL = 3.6 V	-10		10	μΑ	
LVDS inp	uts		•				
	Differential input law threehold	V <sub>CM</sub> = 1.2 V			-100	- m\/	
$V_{TL}$	Differential input low threshold	-4 V < V <sub>CM</sub> < +5 V			-130		
\/	/ Differential insult high thus shald	V <sub>CM</sub> = 1.2 V	+100			mV	
$V_{TH}$	Differential input high threshold	-4 V < V <sub>CM</sub> < +5 V	+130				
V <sub>CL</sub>	TTL input clamp voltage	I <sub>CL</sub> = 18 mA			1.5	V	
$V_{CMR}$	Common mode voltage range	V <sub>ID</sub> = 200 mVp-p	- 4		+5	V	
$V_{CMREJ}$	Common mode rejection <sup>(1)</sup>	F = 10 MHz			300	mVp-p	
I <sub>ID</sub>	Differential input current	V <sub>ID</sub> = 400 mVp-p	-10		10		
I <sub>ICM</sub>	Common mode input current	V <sub>IC</sub> = -4 V to +5 V	-70		70	μΑ	
I <sub>OFFIN</sub>	LVDS input power-off leakage current <sup>(2)</sup>	$V_{CC} = 0 \text{ V}, V_{IN} = -4 \text{ V to 5 V}$	-60		60		
C <sub>IN</sub>	Input capacitance			3		pF	
LVDS out	puts						
V <sub>OH</sub>	Output voltage high				1.65	V	
V <sub>OL</sub>	Output voltage low		0.925			V	
V <sub>OD</sub>	Differential output voltage		250		400		
DV <sub>OD</sub>	Change of magnitude of V <sub>OD</sub> for complementary output states				10	mV	
V <sub>OS</sub>	Offset voltage		1.125		1.45	٧	

Table 7. Electrical characteristics table (continued)

Complementary output states    IoS   Output short-circuit current   VID = -400 mV and VOUT. = 0 V   -9   m.	Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Comparison   Com	DV <sub>OS</sub>					25	mV
LVDS outputs power-off leakage current   V <sub>CC</sub> = 0 V, V <sub>OUT</sub> = 3.6 V   -50   +50     +50       T <sub>S</sub>	I <sub>OS</sub>	Output short-circuit current	$V_{ID}$ = -400 mV and $V_{OUT}$ = 0 V $V_{ID}$ = +400 mV and $V_{OUT}$ = 0 V	-9			mA
$ \begin{array}{ c c c c } \hline \textbf{OFFOUT} & \textbf{Current} & \textbf{VCC} = 0 \text{ V, VOUT} = 3.6 \text{ V} & -50 & +50 $	I <sub>OZ</sub>	High impedance output current	Disabled, V <sub>OUT</sub> = 3.6 V or 0V	-10		10	
T <sub>H</sub> Input to SL Hold time <sup>(3)</sup> T <sub>Sw</sub> SL to Switched output <sup>(3)</sup> t <sub>PHLD</sub> Propagation delay time, high to low  t <sub>PLHD</sub> Propagation delay time, low to high  t <sub>SK1</sub> Channel to channel skew <sup>(3)(4)</sup> t <sub>SK2</sub> Chip to chip skew <sup>(3)(5)</sup> V <sub>ID</sub> = 200 mVp-p, input pulse from 1.5 4  1.5 4  1.5 4  1.5 4  1.5 4  1.5 4  1.5 0.6  V <sub>ID</sub> = 200 mVp-p  Load: refer to Figure 3  1.5 0.6  V <sub>ID</sub> = 200 mVp-p  Load: refer to Figure 6  1.5 0.6  T <sub>SKD</sub> Differential skew <sup>(6)</sup> (t <sub>PHLD</sub> -t <sub>PLHD</sub> )  t <sub>T</sub> Output signal rise time  t <sub>T</sub> Output signal rise time  t <sub>PLZ</sub> Propagation delay time, low level to high impedance output  t <sub>PLZ</sub> Propagation delay time, high impedance to high level output  t <sub>PZH</sub> Propagation delay time, high impedance to low level output  t <sub>PZH</sub> Propagation delay time, high impedance to low level output  t <sub>PZH</sub> Propagation delay time, high impedance to low level output  t <sub>PZH</sub> Propagation delay time, high impedance to low level output  t <sub>PZH</sub> Propagation delay time, high impedance to low level output  Fail-safe and cold-spare  t <sub>D1</sub> Fail-safe to active time	I <sub>OFFOUT</sub>		V <sub>CC</sub> = 0 V, V <sub>OUT</sub> = 3.6 V	-50		+50	μΑ
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	T <sub>S</sub>	Input to SL setup time <sup>(3)</sup>		1.6			
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	T <sub>H</sub>	Input to SL Hold time <sup>(3)</sup>	Refer to Figure 5	1.5			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	T <sub>Sw</sub>	SL to Switched output <sup>(3)</sup>				5	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	t <sub>PHLD</sub>		V <sub>ID</sub> = 200 mVp-p, input pulse from	1.5		4	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	t <sub>PLHD</sub>			1.5		4	
t <sub>SKD</sub> Differential skew <sup>(6)</sup> (t <sub>PHLD</sub> -t <sub>PLHD</sub> )  t <sub>r</sub> Output signal rise time t <sub>f</sub> Output signal fall time  t <sub>PLZ</sub> Propagation delay time, low level to high impedance output  t <sub>PHZ</sub> Propagation delay time, high impedance to high level output  t <sub>PZH</sub> Propagation delay time, high impedance to high level output  t <sub>PZL</sub> Propagation delay time, high impedance to low level output  t <sub>PZL</sub> Propagation delay time, high impedance to low level output  t <sub>PZL</sub> Propagation delay time, high impedance to low level output  Fail-safe and cold-spare	t <sub>SK1</sub>	Channel to channel skew <sup>(3)(4)</sup>				0.6	
to transfer to Figure 4  to the total propagation delay time, high level to high impedance output  the propagation delay time, high level to high impedance output  the propagation delay time, high level to high impedance output  the propagation delay time, high level to high level output  the propagation delay time, high level output  the propagation d	t <sub>SK2</sub>	Chip to chip skew <sup>(3)(5)</sup>				0.7	
t f Output signal fall time  t pLZ Propagation delay time, low level to high impedance output  t pHZ Propagation delay time, high level to high impedance output  t propagation delay time, high impedance to high level output  t propagation delay time, high impedance to high level output  t propagation delay time, high impedance to low level output  t propagation delay time, high impedance to low level output  Fail-safe and cold-spare  t propagation delay time, high impedance to low level output  Tail-safe and cold-spare	t <sub>SKD</sub>		Load: refer to Figure 6			0.6	ns
t f Output signal fall time  t pLZ Propagation delay time, low level to high impedance output  t pHZ Propagation delay time, high level to high impedance output  t pZH Propagation delay time, high impedance to high level output  t pZL Propagation delay time, high impedance to low level output  t pZL Propagation delay time, high impedance to low level output  Fail-safe and cold-spare  t D1 Fail-safe to active time  0.9  2.8  2.8  2.8  2.8  2.5	t <sub>r</sub>	Output signal rise time	Refer to Figure 4		0.9		
tevel to high impedance output  tend propagation delay time, high level to high impedance output  tend propagation delay time, high impedance to high level output  tend propagation delay time, high impedance to high level output  tend propagation delay time, high impedance to low level output  Fail-safe and cold-spare  tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high impedance to low level output  Tend propagation delay time, high i	t <sub>f</sub>	Output signal fall time	Tielei to Figure 4		0.9		
tevel to high impedance output  Propagation delay time, high impedance to low level output  Fail-safe and cold-spare  tevel to high impedance output  Refer to Figure 6  2.5  2.5	t <sub>PLZ</sub>					2.8	
Propagation delay time, high impedance to high level output  t <sub>PZL</sub> Propagation delay time, high impedance to low level output  Fail-safe and cold-spare  t <sub>D1</sub> Fail-safe to active time  2.5	t <sub>PHZ</sub>		Potor to Figure 6			2.8	
impedance to low level output  Fail-safe and cold-spare  t <sub>D1</sub> Fail-safe to active time  1   µs	t <sub>PZH</sub>		neiei io <i>Figure</i> o			2.5	
t <sub>D1</sub> Fail-safe to active time	t <sub>PZL</sub>					2.5	
μ:	Fail-safe	Fail-safe and cold-spare					
	t <sub>D1</sub>	Fail-safe to active time			1		шс
	t <sub>D2</sub>	Active to fail-safe time			1		μs

- 1. Guaranteed by characterization on bench.
- 2. All pins are floating except pin under test and  $V_{\mbox{\footnotesize CC}}$ .
- 3. Guaranteed by design.
- 4. t<sub>SK1</sub> is the maximum delay time difference between drivers on the same device (with all inputs connected together).
- 5.  $t_{SK2}$  is the maximum delay time difference between outputs of all devices when they operate with the same supply voltage, at the same temperature.
- 6.  $t_{SKD}$  is the maximum delay time difference between  $t_{PHLD}$  and  $t_{PLHD}$  (see Figure 4).



### **Cold sparing**

The RHFLVDS2281 features a cold spare input and output buffer. In high reliability applications, cold sparing enables a redundant device to be tied to the data bus with its power supply at 0 V ( $V_{CC}$  = GND) without affecting the bus signals or injecting current from the I/Os to the power supplies. Cold sparing also allows redundant devices to be kept powered off so that they can be switched on only when required. This has no impact on the application. Cold sparing is achieved by implementing a high impedance between the I/Os and  $V_{CC}$ . ESD protection is ensured through a non-conventional dedicated structure.

#### Fail-safe

In many applications, inputs need a fail-safe function to avoid an uncertain output state when the inputs are not connected properly. In case of an LVDS input short circuit or floating inputs, the LVDS outputs remain in stable logic-high state.



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RHFLVDS2281 Test circuit

### 5 Test circuit

Figure 3. Voltage and current definition

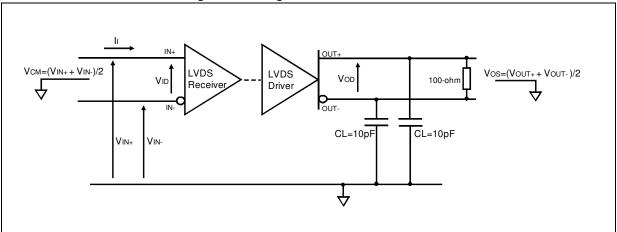
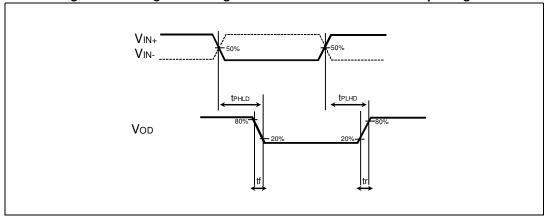


Figure 4. Timing and voltage definitions for differential output signal



- 1. All input pulses are supplied by a generator with the following characteristics:  $t_f$  or  $t_f \le 1$  ns, f=1 MHz,  $Z_O=50$   $\Omega$ , and duty cycle = 50%.
- 2. The product is guaranteed with  $C_L = 10 \text{ pF}$ .

Test circuit RHFLVDS2281

Figure 5. MUX switch timings

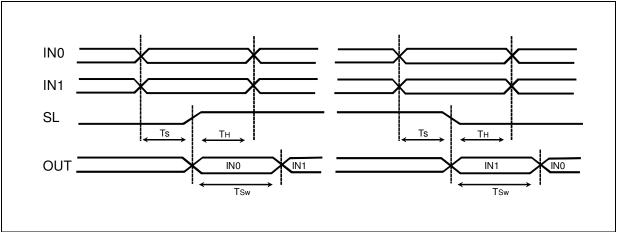
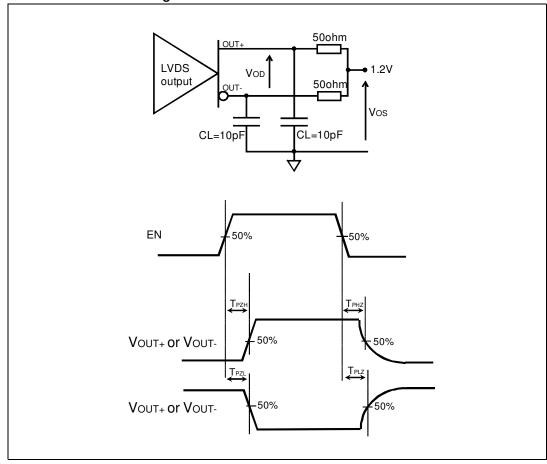


Figure 6. Enable and disable waveforms



1. All input pulses are supplied by a generator with the following characteristics on EN:  $t_r$  or  $t_f \le 1$  ns, F = 500 kHz, pulse width = 500 ns.

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# 6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.



Package information RHFLVDS2281

## 6.1 Ceramic Flat-64 package information

Figure 7. Ceramic Flat 64 package mechanical drawing

1. The upper metallic lid is electrically connected to ground.

Table 8. Ceramic Flat 64 package mechanical data

	Dimensions					
Ref.	Ref.					
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	2.41	2.66	2.92	0.095	0.105	0.115
A1	0.33	-	-	0.013	-	-
b	0.18	0.2	0.23	0.007	0.008	0.009
С	0.15	0.2	0.25	0.006	0.008	0.010
D	20.91	21.11	21.31	0.823	0.831	0.839
E	8.64	8.76	8.89	0.340	0.345	0.350
E2	6.57	6.72	6.87	0.259	0.265	0.270
E3	-	1.02	-	-	0.040	-
е	-	0.635	-	-	0.025	-
L	12.45	12.7	12.95	0.49	0.5	0.51
S1	-	0.61	-	-	0.024	-



#### **Ordering information** 7

Table 9. Order codes

Order code	Description	Temp. range	Package	Marking <sup>(1)</sup>	Packing	
RHFLVDS2281K1	Engineering model	-55 °C to	Ceramic Flat-64	RHFLVDS2281K1	Strip	
RHFLVDS2281K01V	QML-V flight			5962F1423401VXC	pack	

- Specific marking only. Complete marking includes the following: SMD pin (on QML-V flight only)

  - ST logo Date code (date the package was sealed) in YYWWA (year, week, and lot index of week)

  - QML logo (Q or V) Country of origin (FR = France).

Note:

Contact your ST sales office for information regarding the specific conditions for products in die form and QML-Q versions.

#### **Shipping information** 8

#### Date code

The date code is structured as follows:

- Engineering model: EM xyywwz
- QML flight model: FM yywwz

#### Where:

x = 3 (EM only), assembly location Rennes (France)

yy = last two digits of the year

ww = week digits

z = lot index of the week

Revision history RHFLVDS2281

# 9 Revision history

Table 10. Document revision history

Date	Revision	Changes
04-Mar-2015	1	Initial release.
10-Nov-2023	2	Added V <sub>IN</sub> and V <sub>ID</sub> in <i>Table 4: Absolute maximum ratings</i> .

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